

M54HC221/221A M74HC221/221A

DUAL MONOSTABLE MULTIVIBRATOR

- HIGH SPEED
 - $t_{PD} = 25 \text{ ns} (TYP) \text{ at } V_{CC} = 5V$
- LOW POWER DISSIPATION

 STANDBY STATE I_{CC}=4 μA (MAX.) AT T_A=25°C

 ACTIVE STATE I_{CC} = 700 μA (MAX.) AT V_{CC}=5V
- HIGH NOISE IMMUNITY V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE IOH = IOL = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- WIDE OUTPUT PULSE WIDTH RANGE twout = 150 ns ~ 60 s OVER AT V_{CC} = 4.5 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS221

DESCRIPTION

The M54/74HC221/221A are high speed CMOS MONOSTABLE multivibrators fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. There are two trigger inputs, A INPUT (negative edge) and B INPUT (positive edge). Triggering on the B input occurs at a particular voltage threshold and is not related to the rise and fall time of the applied pulse. The device may also be triggered by using the CLR input (positive-edge) because of the Schmitt-trigger input; after triggering the output maintains the MONOSTABLE state for the time period determined by the external resistor Rx and capacitor Cx. Taking CLR low breaks this MONOSTABLE STATE. If the next trigger pulse occurs during the MONOSTABLE period it makes the MONOSTABLE period longer. Limit for values of Cx and Rx:

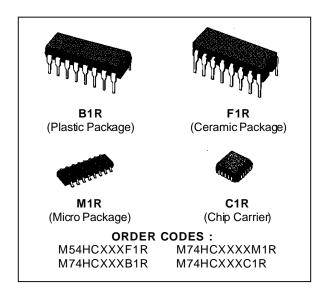
Cx: NO LIMIT

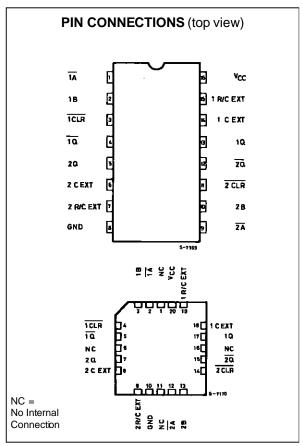
Rx : V_{CC} < 3.0 V 5 K Ω to 1 M Ω V_{CC} \geq 3.0 V 1 K Ω to 1 M Ω

Two different pulse width constants are available:

 $K \cong 0.7$ for $H\dot{C}221$ $K \cong 1$ for HC221A

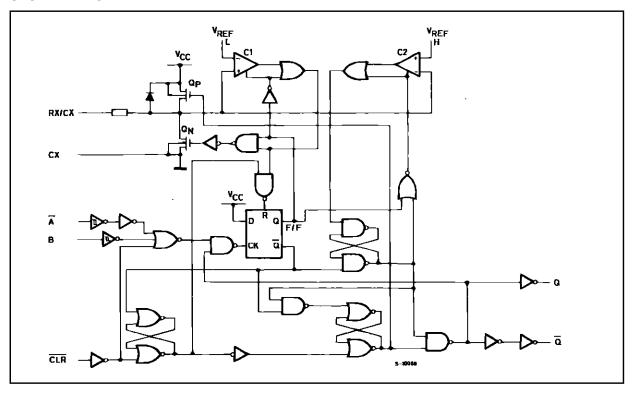
All inputs are equipped with protection circuits against static discharge and transient excess voltage.



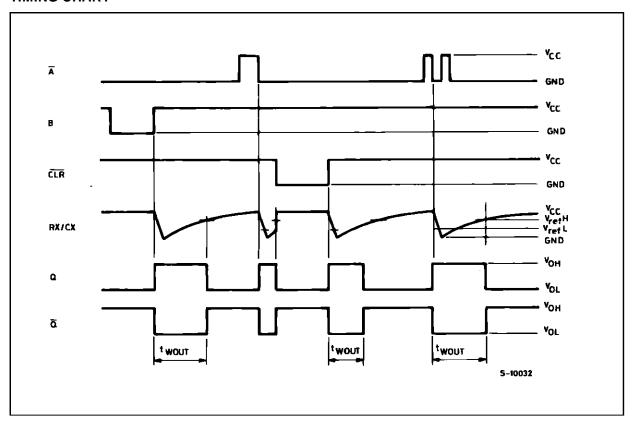


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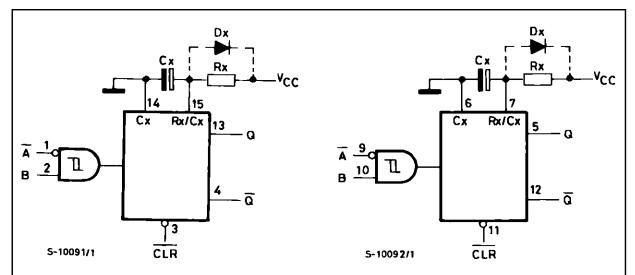
SYSTEM DIAGRAM



TIMING CHART



BLOCK DIAGRAM



Note

- (1) Cx, Rx, Dx are external components.
- (2) Dx is a clamping diode.

The external capacitor is charged to V_{CC} in the stand-by state, i.e. no trigger. When the supply voltage is turned off Cx is discharged mainly through an internal parasitic diode (see figures). If Cx is sufficiently large and V_{CC} decreases rapidy, there will be some possibility of damaging the I.C. with a surge current or latch-up. If the voltage supply filter capacitor is large enough and V_{CC} decrease slowly, the surge current is automatically limited and damage the I.C. is avoided. The maximum forward current of the parasitic diode is approximately 20 mA. In cases where Cx is large the time taken for the supply voltage to fall to 0.4 V_{CC} can be calculated as follows:

 $t_f \geq (V_{CC} - 0.7) \cdot Cx/20mA$

In cases where $t_{\rm f}$ is too short an external clamping diode is required to protect the I.C. from the surge current.

FUNCTIONAL DESCRIPTION

STAND-BY STATE

The external capacitor, Cx, is fully charged to V_{CC} in the stand-by state. Hence, before triggering, transistor Qp and Qn (connected to the Rx/Cx node) are both turned-off. The two comparators that control the timing and the two reference voltage sources stop operating. The total supply current is therefore only leakage current.

TRIGGER OPERATION

Triggering occurs when:

- 1st) A is "low" and B has a falling edge;
- 2nd) B is "high" and A has a rising edge;
- 3rd) A is low and B is high and C1 has a rising edge.

After the multivibrator has been retriggered comparator C1 and C2 start operating and Qn is turned on. Cx then discharges through Qn. The voltage at the node R/C external falls.

When it reaches V_{REFL} the output of comparator C1 becomes low. This in turn resets the flip-flop and Qn is turned off.

At this point C1 stops functioning but C2 continues to operate.

The voltage at R/C external begins to rise with a time constant set by the external components Rx, Cx.

Triggering the multivibrator causes Q to go high after internal delay due to the flip-flop and the gate. Q remains high until the voltage at R/C external rises again to V_{REFH}. At this point C2 output goes low and O goes low. C2 stop operating. That means that after triggering when the voltage R/C external returns to V_{REFH} the multivibrator has returned to its MONOSTABLE STATE. In the case where Rx \cdot Cx are large enough and the discharge time of the capacitor and the delay time in the I.C. can be ignored, the width of the output pulse tw (out) is as follows :

 $t_{W(OUT)} = 0.70 \text{ Cx} \cdot \text{Rx} \text{ (HC221)}$ $t_{W(OUT)} = \text{Cx} \cdot \text{Rx} \text{ (HC221A)}$

RESET OPERATION

CL is normally high. If CL is low, the trigger is not effective because Q output goes low and trigger control flip-flop is reset.

Also transistor Op is turned on and Cx is charged quicky to Vcc. This means if CL input goes low, the IC becomes waiting state both in operating and non operating state.

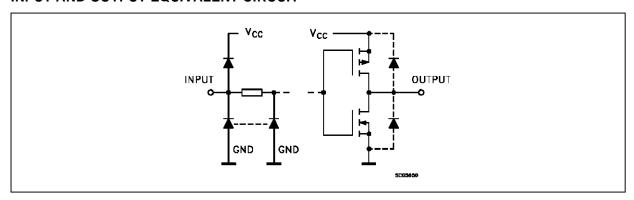


TRUTH TABLE

	INPUTS			PUTS	NOTE
Ā	В	CLR	Ø	Q	NOTE
	Н	Н	<u> </u>		OUTPUT ENABLE
X	L	Н	L (*)	H (*)	INHIBIT
Н	X	Н	L (*)	H (*)	INHIBIT
L		Н	<u> </u>		OUTPUT ENABLE
L	Н		<u> </u>		OUTPUT ENABLE
Х	X	L	L	Н	INHIBIT

X: Don't Care (*): Except for monostble period

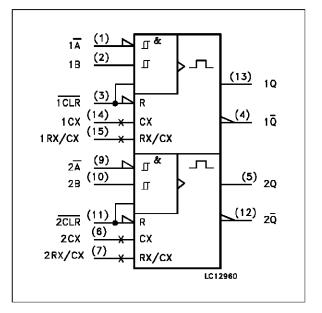
INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 9	1Ā, 2Ā	Trigger Inputs (Negative Edge Triggered)
2, 10	1B, 2B	Trigger Inputs (Positive Edge Triggered)
3, 11	1 <u>CLR,</u> 2CLR	Direct Reset LOW and Trigger Action at Positive Edge
4, 12	1Q, 2Q	Outputs (Active LOW)
7	2R _{EXT} /C _{EXT}	External Resistor Capacitor Connection
13, 5	1Q, 2Q	Outputs (Active HIGH)
14, 6	1C _{EXT} 2C _{EXT}	External Capacitor Connection
15	1R _{EXT} /C _{EXT}	External Resistor Capacitor Connection
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
V_{I}	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \cong 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage		2 to 6	V
V_{I}	Input Voltage	0 to V _{CC}	V	
Vo	Output Voltage		0 to V _{CC}	V
T_{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time (CLR and A only)	V _{CC} = 2 V	0 to 1000	ns
		V _{CC} = 4.5 V	0 to 500	
		$V_{CC} = 6 V$	0 to 400	
C_X	External Capacitor		> 100 (*)	pF
R_X	R _X External Resistor		5K to 1M (*)	Ω
		$V_{CC} \ge 3 \text{ V}$	1K to 1M (*)	

(*)The maximum allowable values of Cx and Rx are a function of leackage of capacitor Cx, the leackage of HC221/A, and leackage due to the board layout and surface resistance. Susceptibility to externally induced noise signals may occur for Rx > $1 \text{M}\Omega$



DC SPECIFICATIONS

		Test Conditions			Value							
Symbol Parameter		Vcc			_A = 25 ^c C and 7			85 °C HC	-55 to 125 °C 54HC		Unit	
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V_{OH}	High Level	2.0	Vı =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI –	I _O =-20 μA	4.4	4.5		4.4		4.4		V
	(Q, Q Output)	6.0	or		5.9	6.0		5.9		5.9		
		4.5	V _{IL}	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	V _I =	_		0.0	0.1		0.1		0.1	
	Voltage	4.5	VIH	I _O = 20 μA		0.0	0.1		0.1		0.1	.,
	(Q, Q Output)	6.0	or			0.0	0.1		0.1		0.1	V
		4.5	VIL	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	Vı = '	Vcc or GND			±0.1		±1		±1	μΑ
II	R/C Terminal Off State Current	6.0	V _I = '	$V_I = V_{CC}$ or GND			±0.5		±5		±10	μΑ
I _{CC}	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			4		40		80	μΑ
I _{CC} '	Active State	2.0	V _I = '	V _{CC} or GND		45	250		260		350	μΑ
	Supply Current (1)	4.5	Vır	$V = V_{CC}/2$		400	530		650		850	μΑ
		6.0				0.7	1		1.3		1.7	mA

(1): Per Circuit



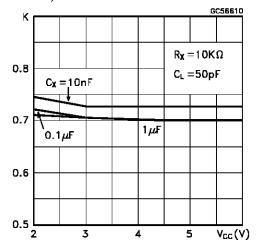
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

		Test Conditions		Value							
Symbol Parameter		Vcc			_A = 25 ^o C and 7		-40 to	85 °C HC	-55 to 125 °C 54HC		Unit
	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t _{TLH} Output Transition	2.0			30	75		95		110		
t_{THL}	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH}	Propagation	2.0			102	210		265		315	
t_{PHL}	Delay Time_	4.5			30	42		53		63	ns
	$(\overline{A}, B - Q, \overline{Q})$	6.0			24	36		45		54	
tpLH	Propagation	2.0			102	235		295		355	
t _{PHL}	Delay Time _	4.5			30	47		59		71	ns
	(CLR TRIGGER - Q, Q)	6.0			24	40		50		60	
tplH	Propagation	2.0			67	160		200		240	
t _{PHL}	Delay Time_	4.5			20	32		40		48	ns
	$(\overline{CLR} - Q, \overline{Q})$	6.0			16	27		34		41	
twout	Output Pulse	2.0	C _X = 100 pF		1.5						
	Width	4.5	$R_X = 10 \text{ K}\Omega$		1.3						μs
	(for HC221)	6.0			1.2						
		2.0	$C_X = 0.1 \mu F$		7						
		4.5	$R_X = 100 \text{ K}\Omega$		6.9						ms
		6.0			6.9						
t _{WOUT}	Output Pulse	2.0	C _X = 100 pF		1.8						
	Width	4.5	$R_X = 10 \text{ K}\Omega$		1.5						μs
	(for HC221A)	6.0			1.4						
		2.0	$C_X = 0.1 \mu F$		10						
		4.5	$R_X = 100 \text{ K}\Omega$		9.7						ms
		6.0			9.6						
Δtwout	Output Pulse Width Error Between Circuits in Same Package				±1						%
t _{W(H)}	Minimum Pulse	2.0				75		95		110	
t _{W(L)}	Width	4.5				15		19		22	ns
		6.0				13		16		20	
$t_{W(L)}$	Minimum Pulse	2.0				75		95		110	
	Width	4.5				15		19		22	ns
		6.0				13		16		20	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				174						pF

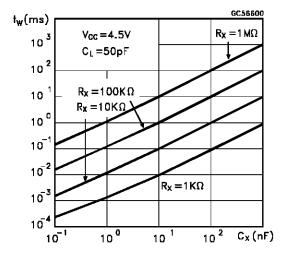
^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ Duty/100 + I_{CC} 2 (per monostable) (Icc': Active Supply Current) (Duty:%)



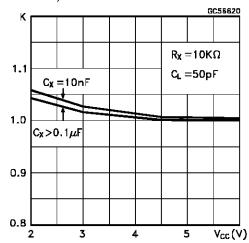
Output Pulse Width Constant Characteristics (for HC221)



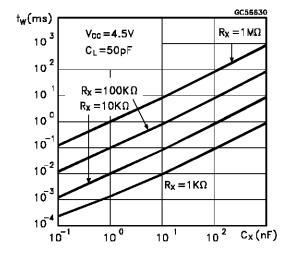
Output Pulse Width Characteristics (for HC221)



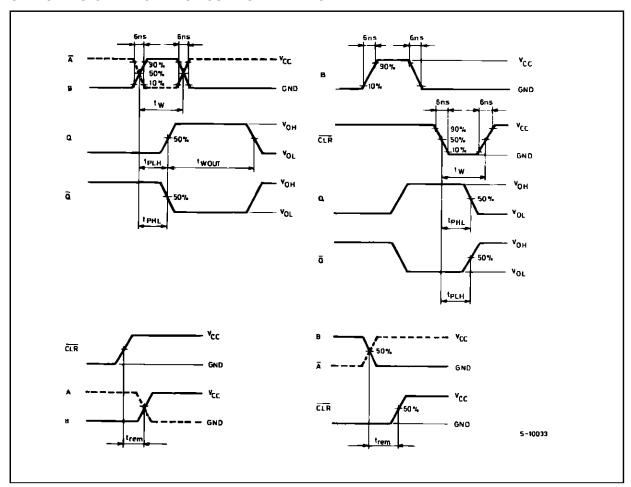
Output Pulse Width Constant Characteristics (for HC221A)



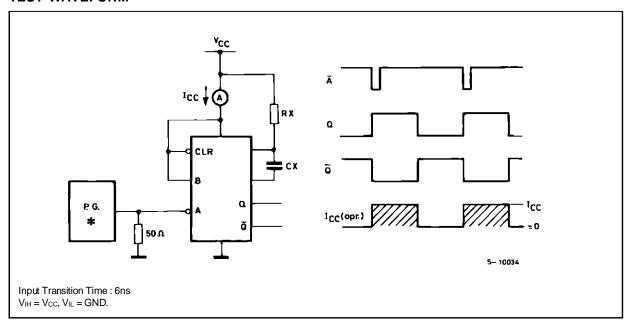
Output Pulse Width Characteristics (for HC221A)



SWITCHING CHARACTERISTICS TEST WAVEFORM

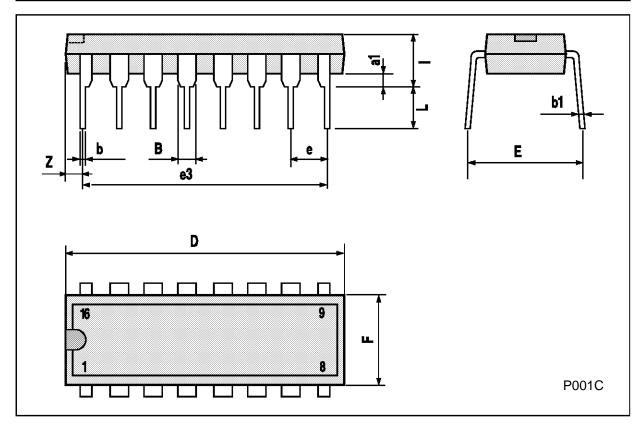


TEST WAVEFORM



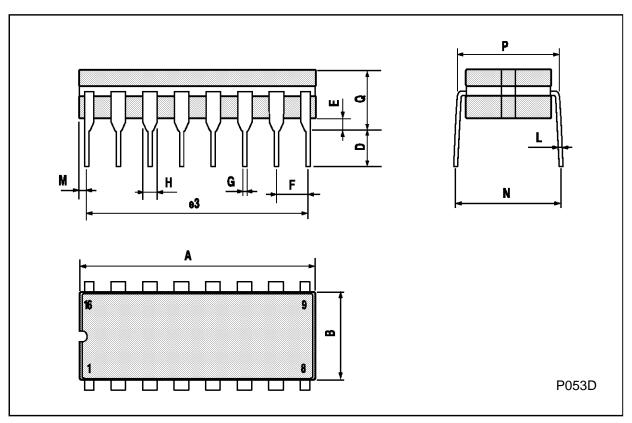
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch			
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z			1.27			0.050	



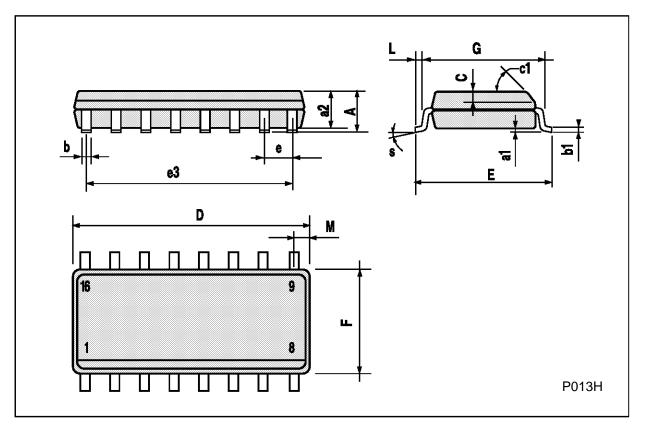
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			20			0.787	
В			7			0.276	
D		3.3			0.130		
Е	0.38			0.015			
e3		17.78			0.700		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
M	0.51		1.27	0.020		0.050	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



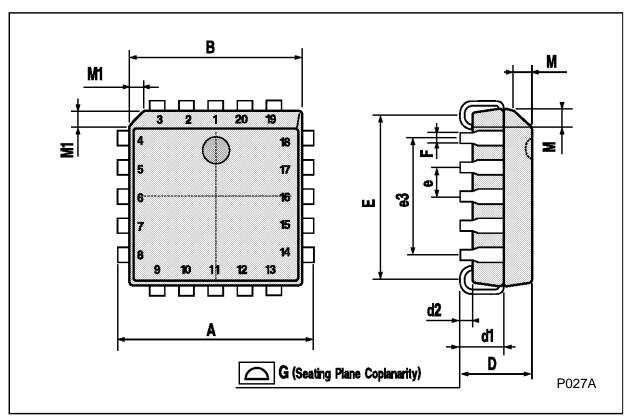
SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch				
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	9.8		10	0.385		0.393		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (r	nax.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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